24. A semiconductor memory according to claim 23 further comprising:

Chy

a fourth switching MOS transistor of N-channel type having a drain coupled to said source of each of said pair of N-channel MOS transistors and a source coupled to said first potential terminal, wherein said fourth switching MOS transistor is turned "on" at a time different from the time when said second switching MOS transistor is turned "on". --

REMARKS

Entry of this Amendment prior to examination is respectfully requested.

By the present Amendment, new claims 20-24 are presented in this case to define additional aspects of the present invention.

If the Examiner believes that there are any other points which may be clarified or otherwise disposed of, either by telephone discussion or by personal interview, he is invited to contact applicants' undersigned attorney at the number indicated below.

To the extent necessary, the applicants petition for an extension of time under 37 CFR 1.136. Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees, to the deposit account of Antonelli, Terry, Stout & Kraus, Deposit Account

